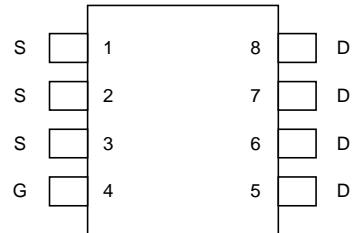


P-Channel Enhancement Mode MOSFET

Features

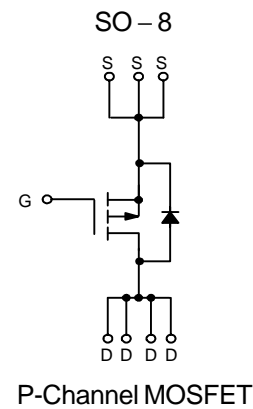
- -30V/-5.3A, $R_{DS(ON)} = 60m\Omega(\text{typ.}) @ V_{GS} = -10V$
 $R_{DS(ON)} = 90m\Omega(\text{typ.}) @ V_{GS} = -4.5V$
- Super High Density Cell Design
- Reliable and Rugged
- SO-8 Package

Pin Description



Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	
I_D	Maximum Drain Current – Continuous	$T_A = 25^\circ\text{C}$ -4.6	A
I_{DM}	Maximum Drain Current – Pulsed	-20	